

**Qualification report 12bit 4.5Gbps MuxDAC  
EV12DS400A – VN62A – FpBGA 196 - THIMS**

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## 1. INTRODUCTION

This document presents the results of all tests that have been carried out by e2v Grenoble to qualify the EV12DS400A family - 12bit 4.5Gsp/s MuxDAC - in FpBGA 196 package according to the following document:

*NE 31S 212 082: Qualification plan - 12bit 4.5Gsp/s MuxDAC - VN62A - EV12DS400A - FpBGA 196 – THIMS*

## 2. APPLICABLE DOCUMENTS

- NE.31S.212082      Qualification plan - 12bit 4.5Gsp/s MuxDAC - VN62A - EV12DS400A - FpBGA 196 – THIMS
- SQ.32S.07680      GUIDE DE QUALIFICATION DES PRODUITS HRS
- JEDEC Standard      Global standards for the microelectronics industry

## 3. PRODUCTS DESCRIPTION

### 3.1 DIE INFORMATION

Product	EV12DS400A
Mask	VN62A
Process name	B7HF200
Process type	200Ghz SiGe Bipolar
Die size	4.58 mm x 4.58 mm (21 mm <sup>2</sup> )
Passivation	SiO <sub>2</sub> (0.3 μm) & SiN (0.55 μm)
Die thickness	300 μm
Last metallization layer	Au (500nm) / Pt (60nm) / Ti (60nm)

### 3.2 PACKAGE INFORMATION

Package	FpBGA 196
Package outline	15 x 15 x 1.2 mm
Pitch	1.00 mm
Die attach material	Ablebond 2000B (green)
Substrate	SCC PHP900 & MCT
Wire	Au 25 μm
Mold Compound	EME G760V (green)
Solder Ball	Sn62/Pb36/Ag2 or SAC305 (Pb-Free)
Flux	WSD 3810 - Umicore
Moisture Level	3 (peak 235°C & 260°C)
P (dissipated power in Watt)	2.6 Watt (in 4:1 MUX)

### 3.3 LOCATION INFORMATION

Wafer fab	Infineon (Germany)
Assy plant	Unisem Batam (Indonesia)
Testing plant	e2v (Grenoble)

#### 4. SYNTHESIS RESULTS

TEST	Acceptable criteria	METHOD	Condition	Sample	Fail	Status
Construction analysis	Infineon B7HF 200 specifications	MIL-STD-883 TM2018	Mask VN62A	6	0	Pass
ESD HBM	ATE program	JESD22-A114E	Class 1C (1000V to < 2000V)	3	0	Pass
Operating Life Test	ATE program	MIL-STD-883 TM1005	1000 Hrs / Tj 167°C	48	0	Pass
ESD MM	ATE program	JESD22-A115-C	Class M2 (100V to < 200V)	3	0	Pass
LATCH UP	ATE program	JEDEC 78B	Class I Class II	3 3	0 0	Pass
Moisture sensitivity Level 3	ATE program Ultrasound scan & transmission	JSTD-020D	Level 3 /30°C 60%RH 192H peak 260°C	24	0	Pass
Temp. Humidity with Bias*	ATE program	JESD22-A101	1000Hrs / 85°C/85% RH/ 7.12Psi	24*	0	Pass
Temperature Cycle*	ATE program Visual inspection	JESD22-A104	500 cy A/A -65°C / 150°	24*	0	Pass
Accelerated Moisture resistance – Unbiased Autoclave	ATE program	JESD22-A102-C	121°C/2atm/100%RH / 168Hrs	Done by similarity**		Pass
Highly Accelerated Stress Test	ATE program Visual inspection	JESD22-A110	96H 130°C/85%RH/2atm Unbiased	Done by similarity**		Pass
High Temperature Storage	ATE program	JESD22-A103-C	1000Hrs / 150°C	Done by similarity**		Pass
Outline measurements	Package spec	FpBGA package outline	Package spec	Done by similarity**		Pass
Ball Shear	Visual inspection	JESD22-B117 & AEC-Q100-010	Min acceptable=500g	Done by similarity**		Pass
Package Construction analysis	Internal visual	Microsections	Package spec	Done by similarity**		Pass

\*Devices Issued from MSL3

\*\*Qualification based on results from same package and die family

#### 5. GENERAL CONCLUSION

The following products have passed with success all tests as defined in test plan ref: NE 31S 212 082.

Products	Package	Termination finish	Max. peak reflow	Temperature range
EV12DS400ACZP	FpBGA 196	Sn62/Pb36/Ag2	235°C	“C” Grade 0°C < Tc ; Tj < 90°C
EV12DS400ACZPY		Sn96.5/Ag3/Cu0.5	260°C	
EV12DS400AVZP		Sn62/Pb36/Ag2	235°C	“V” Grade -40°C < Tc ; Tj < 110°C
EV12DS400AVZPY		Sn96.5/Ag3/Cu0.5	260°C	
EV12DS400AMZP		Sn62/Pb36/Ag2	235°C	“M” Grade -55°C < Tc, Tj < 125°C
EV12DS400AMZPY		Sn96.5/Ag3/Cu0.5	260°C	

## 6. ASSEMBLY LOT INFORMATION

Mask	Diffusion lot	Assy lot ID / WO	Date Code
VN62A	RU516515	4719043 / 4 / 5	1526

## 7. TEST RESULTS

### 7.1 VN62A die results

#### 7.1.1 Construction analysis

TEST <i>Acceptable criteria</i>	METHOD <i>Condition</i>	Sample	Fail	Status
Construction analysis <i>Infineon B7HF 200 specifications</i>	MIL-STD-883 TM2018 <i>Mask VN62A</i>	6	0	Pass

Done by SERMA Technologies, see report "AF15-3287-Report .pdf".

#### 7.1.2 Operating Life Test

TEST <i>Acceptable criteria</i>	METHOD <i>Condition</i>	Sample	Fail	Status
Operating Life Test <i>ATE program</i>	MIL-STD-883 TM1005 <i>1000 Hrs / Tj 167°C</i>	48	0	Pass

Parts issued from a lot of 12 wafers VN62A RU516515-VN62A\_S1423A11

#### 7.1.3 ESD HBM

TEST <i>Acceptable criteria</i>	METHOD <i>Condition</i>	Sample	Fail	Status
ESD HBM <i>ATE program</i>	JESD22-A114E <i>Class 1C (1000V to &lt; 2000V)</i>	3	0	Pass

ESD HBM Qty	ESD Stress	STS	e2v final Amb. Elct.
9	9	0	3
2	250V	stressed	ok
3	250V	stressed	ok
4	250V	stressed	ok
5	500V	stressed	ok
6	500V	stressed	ok
7	500V	stressed	ok
8	1000V	stressed	ok
9	1000V	stressed	ok
10	1000V	stressed	ok

Done by STS USA on a lot with DC 1345, see report "171450 HBM Report Rev B- E2V - EV12DS400A\_THIMS.PDF".

7.1.4 ESD MM

TEST	Acceptable criteria	METHOD	Condition	Sample	Fail	Status
ESD MM	ATE program	JESD22-A115-C	Class M2 (100V to < 200V)	3	0	Pass

ESD MM Qty	ESD Stress	STS	e2v final Amb. Elct.
9	9	0	3
11	100V	stressed	ok
12	100V	stressed	ok
13	100V	stressed	ok
14	200V	stressed	Fail O/S
15	200V	stressed	Fail O/S
16	200V	stressed	Fail O/S
17	400V	stressed	Fail O/S
18	400V	stressed	Fail O/S
19	400V	stressed	Fail O/S

Done by STS USA on a lot with DC 1345, see report “171451 MM Report Rev B- E2V - EV12DS400A\_THIMS.PDF”.

7.1.5 LATCH UP

TEST	Acceptable criteria	METHOD	Condition	Sample	Fail	Status
LATCH UP	ATE program	JEDEC 78B	Class I Class II	3 3	0 0	Pass

LU Qty	LU Stress	STS	e2v final Amb. Elct.
6	3+3	0	3+3
20	Ambient Temp.	stressed	ok
21	Ambient Temp.	stressed	ok
22	Ambient Temp.	stressed	ok
23	High Temp.	stressed	ok
24	High Temp.	stressed	ok
25	High Temp.	stressed	ok

Done by STS USA on a lot with DC 1345, see report “171459 Latch Up Test Report Rev B - E2V - EV12DS400A-THIMS.PDF”.

**Conclusion:**

*EV12DS400Axxx product mask VN62A has successfully passed SEM analysis, Life test, ESD and Latch up tests.*

## 7.2 FpBGA 196 Package tests

In order to test the package FpBGA 196, the following tests have been done sequentially on the same 24 parts issued from the original lot with **DC 1526**:

<b>Thermal test – Phase 1</b>					
Step	Test	Method	Condition	CA / CR	Fail / Ok
1	Electrical test	Prog: EV12DS400A	Ambient temperature	24 / 0	Pass
2	<b>Moisture sensitivity Level 3</b>	JSTD-020D	Level 3 /30°C 60%RH 192H peak 260°C	24 / 0	Pass
3	Electrical test	Prog: EV12DS400A	Ambient temperature	24 / 0	Pass
4	<b>Temp. Humidity with Bias</b>	JESD22-A101	1000Hrs / 85°C/85% RH/ 7.12Psi	24 / 0	Pass
5	Electrical test	Prog: EV12DS400A	Ambient temperature	24 / 0	Pass
<b>Then for reliability evaluation (on same devices) - Phase 2</b>					
6	<b>Temperature Cycle</b>	JESD22-A104 / MIL -STD-883 TM1010	500 cy A/A -65°C / 150°	24 / 0	Pass
7	Electrical test	Prog: EV12DS400A	Ambient temperature	24 / 0	Pass
8	Ext. Visual insp.	ESCC 20500		24 / 0	Pass

Tests 2 **MSL 3** and 4 **THB** were done by HIREX, France, see report “PVT\_07308\_01 (MSL).pdf” for test 2 and “Feuille Suivi THB 1000Hrs.pdf” for test 4.

### **Conclusion:**

***EV12DS400Axxx products with package FpBGA have successfully passed temperature and reliability tests.***